

Search History (8pp.) ~~4/2/05~~ (4/2/05).

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S2	244	(nitridization nitride nitriding nitridizing) near4 (ald atomic adj layer adj deposition)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/18 07:41
S3	18	(nitridization nitride nitriding nitridizing) near6 (ald atomic adj layer adj deposition) near6 (ammonia "NH.sub.3")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/17 15:01
S4	1	(nitridization nitride nitriding nitridizing) near6 (ald atomic adj layer adj deposition) and ("without" near3 (ammonia "NH.sub.3"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/17 15:02
S5	179	(nitridization nitride nitriding nitridizing) and silicon adj nitride and ("without" near3 (ammonia "NH.sub.3"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/17 15:03
S6	96	(nitridization nitride nitriding nitridizing) and silicon adj nitride and (spacer barrier) and ("without" near3 (ammonia "NH.sub.3"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/17 15:03
S7	4	(nitridization nitride nitriding nitridizing) and silicon adj nitride and (spacer barrier) and ("without" near3 (ammonia "NH.sub.3")) and (ald atomic adj layer adj deposition)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/17 15:05
S8	4	(nitridization nitride nitriding nitridizing) and ("Si.sub.3 N.sub.4" silicon adj nitride) and (spacer barrier) and ("without" near3 (ammonia "NH.sub.3")) and (ald atomic adj layer adj deposition)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/17 15:06
S9	4	(nitridization nitride nitriding nitridizing) and ("Si.sub.3N.sub.4" silicon adj nitride) and (spacer barrier) and ("without" near3 (ammonia "NH.sub.3")) and (ald atomic adj layer adj deposition)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/17 15:06
S10	4	(nitridization nitride nitriding nitridizing) and ("Si.sub.3"\$1"N.sub.4" silicon adj nitride) and (spacer barrier) and ("without" near3 (ammonia "NH.sub.3")) and (ald atomic adj layer adj deposition)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/17 15:06

S11	4	("Si.sub.3"\$1"N.sub.4" silicon adj nitride) and (spacer barrier) and ("without" near3 (ammonia "NH.sub.3")) and (ald atomic adj layer adj deposition)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/17 15:06
S12	5	("Si.sub.3"\$1"N.sub.4" silicon adj nitride) and ("without" near3 (ammonia "NH.sub.3")) and (ald atomic adj layer adj deposition)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/17 15:07
S13	171	(ald atomic adj layer adj deposition).ti,ab,clm. and silicon adj nitride.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/17 15:08
S14	2	(ald atomic adj layer adj deposition).ti,ab,clm. and silicon adj nitride.ti,ab,clm. and ("without" near4 (ammonia "NH.sub.3"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/17 15:10
S15	31	pdf adj solutions.as.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/17 15:10
S16	0	pdf adj solutions.as. and nitride.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/17 15:21
S17	2691	((257/288) or (257/408) or (257/409) or (257/410) or (257/411)).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2004/10/19 08:37
S18	3	((((257/288) or (257/408) or (257/409) or (257/410) or (257/411)).CCLS.) and "without" near3 (ammonia "NH.sub.3"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/19 08:38
S19	1	((((257/288) or (257/408) or (257/409) or (257/410) or (257/411)).CCLS.) and "without" near3 (ammonia "NH.sub.3") and (lightly adj doped adj drain lightly-doped adj drain ldd)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/17 15:26
S20	5	((((257/288) or (257/408) or (257/409) or (257/410) or (257/411)).CCLS.) and (ald atomic adj layer adj deposition) and (ldd lightly adj doped adj drain) and (silicon adj nitride "Si.sub.3"\$1"N.sub.4" SiN)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/17 15:36

S21	0	((257/288) or (257/408) or (257/409) or (257/410) or (257/411)).CCLS.) and (nitride near4 ("without" near4 (ammonia "NH.sub.3"))) and (ldd lightly adj doped adj drain) and (silicon adj nitride "Si.sub.3"\$1"N.sub.4" SiN)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/17 15:37
S22	1	((257/288) or (257/408) or (257/409) or (257/410) or (257/411)).CCLS.) and ("without" near4 (ammonia "NH.sub.3")) and (ldd lightly adj doped adj drain) and (silicon adj nitride "Si.sub.3"\$1"N.sub.4" SiN)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/17 15:42
S23	0	((257/288) or (257/408) or (257/409) or (257/410) or (257/411)).CCLS.) and ("without" near4 (ammonia "NH.sub.3")) and (ldd lightly adj doped adj drain) and (silicon adj nitride "Si.sub.3"\$1"N.sub.4" SiN) and spacer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/17 15:49
S24	0	(NO-nitridi?ation "N.sub.2"\$1O-nitridi?ation) and silicon adj nitride and (roxnox ono oxide-nitride-oxide "oxide/nitride/oxide") and (lightly adj doped adj drain ldd)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/17 15:52
S25	0	(NO-nitridi?ation "N.sub.2"\$1O-nitridi?ation) and silicon adj nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/17 15:52
S26	4	((NO "N.sub.2"\$1O) near3 nitridi?ation) and silicon adj nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/17 16:00
S27	0	(atomic adj layer adj deposition ald pecvd plasma adj enhanced adj chemical adj vapo\$r adj deposition) near5 "N.sub.2" near5 ("SiCl.sub.4" "SiF.sub.4") and (ono roxnox oxide-nitride-oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/17 16:03
S28	12	(atomic adj layer adj deposition ald pecvd plasma adj enhanced adj chemical adj vapo\$r adj deposition) near5 "N.sub.2" near5 ("SiCl.sub.4" "SiF.sub.4")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/17 16:08

S29	282	method near6 ono.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/17 16:09
S30	0	method near6 ono.clm. and silicon adj nitride and (nitridization nitridisation) near4 (ald atomic adj layer adj deposition pecvd)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/17 16:10
S31	207	method near6 ono.clm. and silicon adj nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/17 16:10
S32	22	method near6 ono.clm. and silicon adj nitride and (lightly adj doped adj drain ldd)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/17 16:13
S33	1	method near6 ono.clm. and silicon adj nitride and ("SiF.sub.4" "SiCl. sub.4") and (lightly adj doped adj drain ldd)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/17 16:21
S34	13	penetration near4 nitrogen and (ono roxnox oxide-nitride-oxide) and silicon adj nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/17 16:52
S35	1	N-containing adj gas and silicon adj nitride and spacer and (ldd lightly adj doped adj drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/17 16:56
S36	1	N-containing adj gas and silicon adj nitride and spacer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/17 16:56
S37	8	N-containing adj gas and silicon adj nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/17 16:57
S38	311	method near3 (ono oxide-nitride-oxide roxnox)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/17 16:58

S39	137	method near3 (ono oxide-nitride-oxide roxnox).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/17 17:18
S40	85	(oxide-nitride-oxide ono roxnox) and (ldd lightly adj doped adj drain) and spacer and etch adj stop	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/17 17:27
S41	8	etch adj stop adj layer near3 silicon adj nitride and silicon adj nitride near4 barrier and (ldd lightly adj doped adj drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/17 17:56
S42	112	(ldd lightly adj doped adj drain).ti,ab,clm. and silicon adj nitride and ono and "438"/\$9.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/17 18:00
S43	0	(ldd lightly adj doped adj drain).ti,ab,clm. and silicon adj nitride and ono and "438"/\$9.ccls. and (ald atomic adj layer adj deposition)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/17 18:01
S44	17	(ldd lightly adj doped adj drain).ti,ab,clm. and silicon adj nitride and ono and "438"/\$9.ccls. and (ald atomic adj layer adj deposition pecvd)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/17 18:01
S45	17	(ldd lightly adj doped adj drain).ti,ab,clm. and silicon adj nitride and ono and "438"/\$9.ccls. and (ald atomic adj layer adj deposition pecvd plasma adj enhanced adj chemical adj vapor adj deposition)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/17 18:02
S46	1	double near4 silicon adj nitride and (ono roxnox oxide-nitride-oxide) and spacer and (ldd lightly adj doped adj drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/18 07:46
S47	4	double near4 silicon adj nitride and (ono roxnox oxide-nitride-oxide) and spacer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/18 07:47
S48	84	method near4 silicon adj nitride near4 spacer and (ldd lightly adj doped adj drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/18 07:51

S49	3	method near4 silicon adj nitride near4 spacer and (ldd lightly adj doped adj drain) and (ald atomic adj layer adj deposition)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/18 08:25
S50	3	(method near4 silicon adj nitride near4 spacer and (ldd lightly adj doped adj drain) and (ald atomic adj layer adj deposition)) and (nitride adj oxide NO "N.sub.2O")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/18 08:28
S51	0	(method near4 silicon adj nitride near4 spacer and (ldd lightly adj doped adj drain) and (ald atomic adj layer adj deposition)) and (nitride adj oxide "N.sub.2O")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/18 08:29
S52	0	(method near4 nitridization and (ldd lightly adj doped adj drain) and (ald atomic adj layer adj deposition)) and (nitride adj oxide "N.sub.2O")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/18 08:29
S53	0	(method near4 nitridization) and (ldd lightly adj doped adj drain) and (ald atomic adj layer adj deposition) and (nitride adj oxide "N.sub.2O")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/18 08:30
S54	0	(method near4 nitridization) and (ald atomic adj layer adj deposition) and (nitride adj oxide "N.sub.2O")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/18 08:30
S55	0	(method near4 nitridization) near6 (nitride adj oxide "N.sub.2O")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/18 08:30
S56	0	method near4 nitridization and ("no" adj2 ammonia)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/18 08:31
S57	47	method near4 nitridization	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/18 08:31
S58	14	(method near4 nitridization).ti,ab, clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/18 08:31

S59	3	((method near4 nitridization).ti,ab,clm.) not (ammonia "NH.sub.3")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/18 08:32
S60	3	((method near4 nitridization).ti,ab,clm.) not (ammonia "NH.sub.3") and method near4 nitridization	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/18 08:36
S61	16	(US-6756634-\$ or US-6436848-\$ or US-5674788-\$ or US-6690046-\$ or US-6744098-\$ or US-6649543-\$ or US-6323519-\$ or US-6653184-\$ or US-6682979-\$ or US-6686298-\$ or US-5734185-\$).did. or (US-20040146644-\$ or US-20040137742-\$ or US-20030143792-\$ or US-20020137296-\$ or US-20040042307-\$).did.	US-PGPUB; USPAT	OR	OFF	2004/10/18 09:17
S62	0	((US-6756634-\$ or US-6436848-\$ or US-5674788-\$ or US-6690046-\$ or US-6744098-\$ or US-6649543-\$ or US-6323519-\$ or US-6653184-\$ or US-6682979-\$ or US-6686298-\$ or US-5734185-\$).did. or (US-20040146644-\$ or US-20040137742-\$ or US-20030143792-\$ or US-20020137296-\$ or US-20040042307-\$).did.) and fu. in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/18 09:36
S63	27	Idd and spacer and silicon adj nitride and ono and ild	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/18 10:16
S64	28	ild near4 protect\$3 and gate and silicon adj nitride and spacer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/18 10:16
S65	2	("20020146879").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/18 15:19
S66	2890	((257/288) or (257/408) or (257/409) or (257/410) or (257/411) or (438/230)).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2004/10/19 08:37

S67	3	((257/288) or (257/408) or (257/409) or (257/410) or (257/411) or (438/230)).CCLS.) and "without" near3 (ammonia "NH.sub.3")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/19 08:38
S98	16	(US-20040042307-\$ or US-20040146644-\$ or US-20030143792-\$ or US-20020137296-\$ or US-20040137742-\$).did. or (US-6690046-\$ or US-6744098-\$ or US-6756634-\$ or US-5734185-\$ or US-6323519-\$ or US-6653184-\$ or US-6682979-\$ or US-5674788-\$ or US-6686298-\$ or US-6436848-\$ or US-6649543-\$).did.	US-PGPUB; USPAT	OR	OFF	2005/04/01 07:16
S99	2	("20020146879").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/01 07:16
S100	18	(US-20040042307-\$ or US-20040146644-\$ or US-20030143792-\$ or US-20020146879-\$ or US-20020137296-\$ or US-20040137742-\$).did. or (US-6690046-\$ or US-6744098-\$ or US-6756634-\$ or US-5734185-\$ or US-6323519-\$ or US-6653184-\$ or US-6682979-\$ or US-5674788-\$ or US-6686298-\$ or US-6436848-\$ or US-6649543-\$).did. or (US-20020146879-\$).did.	US-PGPUB; USPAT; DERWENT	OR	OFF	2005/04/01 09:28
S101	794	(ald atomic adj layer adj deposition) and ammonia	US-PGPUB; USPAT; DERWENT	OR	OFF	2005/04/01 09:29
S102	84	(ald atomic adj layer adj deposition) near10 ammonia	US-PGPUB; USPAT; DERWENT	OR	OFF	2005/04/01 09:37
S103	6	"644633".ap.	US-PGPUB; USPAT; DERWENT	OR	OFF	2005/04/01 09:54
S104	0	ONO adj spacer.ti,ab,clm. and MOSFET.ti,ab,clm.	US-PGPUB; USPAT; DERWENT	OR	OFF	2005/04/01 09:54
S105	2	ONO adj spacer and MOSFET.ti, ab,clm.	US-PGPUB; USPAT; DERWENT	OR	OFF	2005/04/01 09:54